imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

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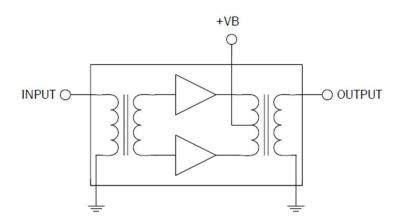




D10040230PL1

GaAs/GaN Power Doubler Hybrid 45MHz to 1000MHz

The D10040230PL1 is a Hybrid Power Doubler amplifier module. The part employs GaAS pHEMT and GaN pHEMT die, has high output capability, and is operated from 45MHz to 1000MHz. It provides excellent linearity and superior return loss performance with low noise and optimal reliability.



Ordering Information

D10040230PL1 Box with 50 pieces

Absolute Maximum Ratings

Parameter	Rating	Unit
RF Input Voltage (single tone)	60	dBmV
DC Supply Over-Voltage (5 minutes)	30	V
Storage Temperature	-40 to +100	°C
Operating Mounting Base Temperature	-30 to +100	°C



Package: SOT-115J

Features

- Low Current
- Excellent Linearity
- Superior Return Loss Performance
- Extremely Low Distortion
- Optimal Reliability
- Extremely Low Noise
- Unconditionally Stable Under All Terminations
- High Output Capability
- 22.5dB Min. Gain at 1GHz
- 380mA Max. at 24VDC

Applications

 45MHz to 1000MHz CATV Amplifier Systems



Caution! ESD sensitive device.



RoHS (Restriction of Hazardous Substances): Compliant per EU Directive 2011/65/EU.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RF Micro Devices Inc. 7628 Thorndike Road, Greensboro, NC 27409-9421

For sales or technical support, contact RFMD at +1.336.678.5570 or customerservice@rfmd.com.

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Nominal Operating Parameters

Parameter	Specification		Unit			
	Min	Тур	Max	Unit	Condition	
General Performance					$V_{+} = 24V; T_{MB} = 30^{\circ}C; Z_{S} = Z_{L} = 75\Omega$	
Power Gain	21.0	21.5	22.0	dB	f = 45MHz	
	22.5	23.0	24.0	dB	f = 1000MHz	
Slope ^[1]	1.0	1.5	2.5	dB	f = 45MHz to 1000MHz	
Flatness of Frequency Response			0.8	dB	f = 45MHz to 1000MHz (Peak to Valley)	
Input Return Loss	20			dB	f = 45MHz to 320MHz	
	19			dB	f = 320MHz to 640MHz	
	18			dB	f = 640MHz to 870MHz	
	16			dB	f = 870MHz to 1000MHz	
Output Return Loss	20			dB	f = 45MHz to 320MHz	
	19			dB	f = 320MHz to 640MHz	
	18			dB	f = 640MHz to 870MHz	
	17			dB	f = 870MHz to 1000MHz	
Noise Figure		3.0	4.0	dB	f = 50MHz to 1000MHz	
Total Current Consumption (DC)		370.0	380.0	mA		
Distortion Data 40MHz to 550MHz					$V_{+} = 24V; T_{MB} = 30^{\circ}C; Z_{S} = Z_{L} = 75\Omega$	
СТВ		-70	-67	dBc		
XMOD		-65	-62	dBc	79 ch 7 dB tilted; V_0 = 50dBmV at 550MHz, plus 75 digital channels (-6dB offset) ^[2]	
CSO		-71	-68	dBc		
CIN	58	62		dB		

1. The slope is defined as the difference between the gain at the start frequency and the gain at the stop frequency.

2. 79 analog channels, NTSC frequency raster: 55.25MHz to 547.25MHz, +43dBmV to +50dBmV tilted output level, plus 75 digital channels, -6dB offset relative to the equivalent analog carrier.

Composite Second Order (CSO) - The CSO parameter (both sum and difference products) is defined by the NCTA.

Composite Triple Beat (CTB) - The CTB parameter is defined by the NCTA.

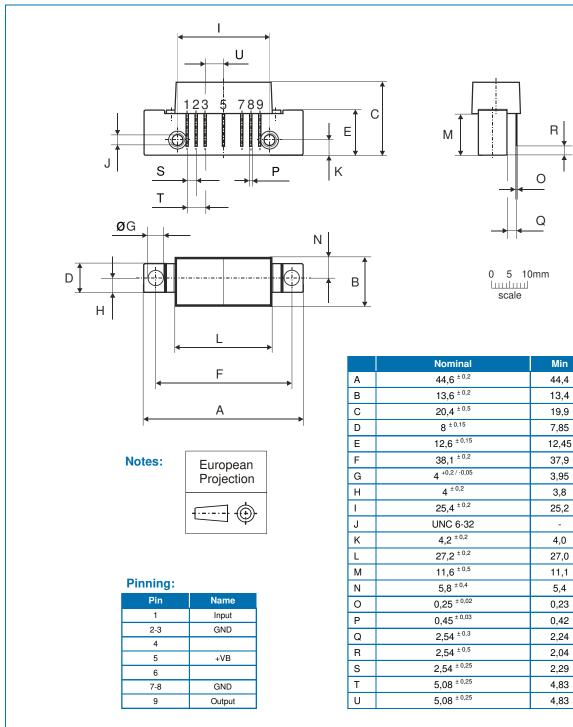
Cross Modulation (XMOD) - Cross modulation (XMOD) is measured at baseband (selective voltmeter method), referenced to 100% modulation of the carrier being tested.

Carrier to Intermodulation Noise (CIN) - The CIN parameter is defined by ANSI/SCTE 17 (Test procedure for carrier to noise).

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Package Drawing (Dimensions in millimeters)



RF Micro Devices Inc. 7628 Thorndike Road, Greensboro, NC 27409-9421

DS131218

Max

44,8

13,8

20,9

8,15

12.75

38,3

4,2

4,2

25,6

_

4,4

27,4

12,1

6,2

0,27

0,48

2,84

3,04

2,79

5,33

5,33

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